



Product Summary

V _{(BR)DSS}	R _{DS(on)}	Ι _D T _A = +25°C
60V	120mΩ @ V _{GS} = 10V	4.4A
	180mΩ @ V _{GS} = 4.5V	3.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control
- Uninterrupted power supplies

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

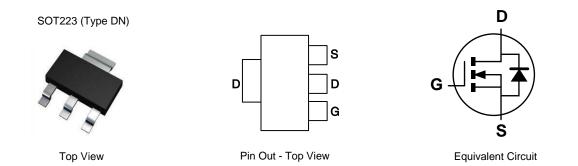
- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A11GTA	See below	7	12	1,000

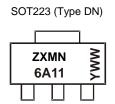
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



ZXMN6A11 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 2= 2022) WW or $\overline{W}W = Week Code (01~53)$

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current	V _{GS} = 10V	(Note 6) T _A = +70°C (Note 6) (Note 5)	ID	4.4 3.5 3.1	
Pulsed Drain Current	$V_{GS} = 10V$	(Note 7)	I _{DM}	15.6	A
Continuous Source Current (Body Diode) (Note 6		(Note 6)	Is	4.4	
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	15.6		

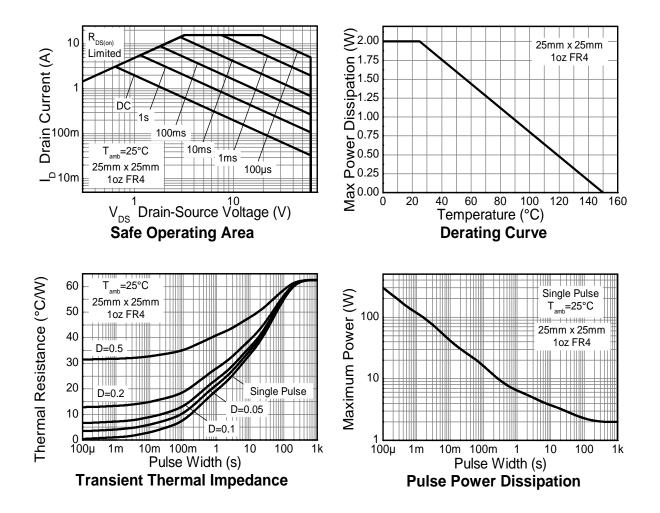
Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		2.0 16	W mW/°C	
Linear Derating Factor	(Note 6)	P _D	3.9 31		
Thermal Resistance, Junction to Ambient	(Note 5) (Note 6)	R _{θJA}	62.5 32.0	°C/W	
Thermal Resistance, Junction to Lead	(Note 8)	R _{θJL}	9.8		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is Notes: measured when operating in a steady-state condition. 6. Same as Note 5, except the device is measured at t \leq 10 seconds. 7. Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300µs. 8. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics





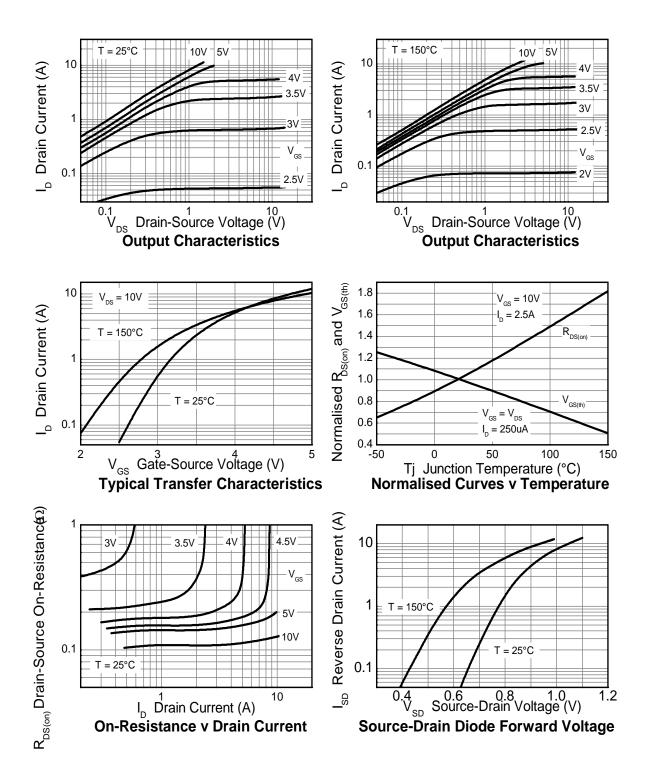
Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test (Condition	
OFF CHARACTERISTICS	Cymbol		1.7b	Mux	Onit	1051 0	Jonandon	
Drain-Source Breakdown Voltage	BV _{DSS}	60			V	I _D = 250μA, V _{GS} = 0V		
Zero Gate Voltage Drain Current	I _{DSS}	_		1.0	μA	$V_{DS} = 60V, V_{GS}$		
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_D$	s = 0V	
ON CHARACTERISTICS								
Gate Threshold Voltage	V _{GS(th)}	1.0		3.0	V	$I_{D} = 250 \mu A, V_{DS}$	s = V _{GS}	
Static Drain-Source On-Resistance (Note 6)		_	0.105	0.120	Ω	$V_{GS} = 10V, I_{D} =$	2.5A	
Static Drain-Source On-Resistance (Note 8)	R _{DS(on)}	_	0.150	0.180		$V_{GS} = 4.5V, I_{D} =$	$V_{GS} = 4.5V, I_D = 2A$	
Forward Transconductance (Notes 6 & 7)	g fs	_	4.9		S	$V_{DS} = 15V, I_D = 2.5A$		
Diode Forward Voltage (Note 6)	V _{SD}	_	0.85	0.95	V	I _S = 2.8A, V _{GS} = 0V, T _J = +25°C		
Reverse Recovery Time (Note 7)	t _{rr}	_	21.5		ns	I _S = 2.8A, di/dt = 100A/μs T _J = +25°C		
Reverse Recovery Charge (Note 7)	Q _{rr}	_	20.5		nC			
DYNAMIC CHARACTERISTICS (Note 7)								
Input Capacitance	C _{iss}	_	330			$V_{DS} = 40V, V_{GS} = 0V,$ f = 1.0MHz		
Output Capacitance	C _{oss}	_	35.2		pF			
Reverse Transfer Capacitance	Crss	_	17.1					
Gate Charge (Note 8)	Qg	_	3.0			$V_{GS} = 4.5V$		
Total Gate Charge (Note 8)	Qg		5.7		nC	$V_{GS} = 10V \qquad V_{DS} = 15V \\ I_D = 2.5A$	$V_{DS} = 15V$	
Gate-Source Charge (Note 8)	Q _{gs}	_	1.25		nc		$I_{D} = 2.5A$	
Gate-Drain Charge (Note 8)	Q _{gd}	_	0.86					
Turn-On Delay Time (Note 8)	t _{D(on)}	_	1.95					
Turn-On Rise Time (Note 8)	tr	_	3.5		$V_{DD} = 30V, I_D = 2.$		2.5A,	
Turn-Off Delay Time (Note 8)	t _{D(off)}		8.2		ns	$R_G = 6\Omega, V_{GS} = 10V$		
Turn-Off Fall Time (Note 8)	t _f		4.6		1			

 Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
For design aid only, not subject to production testing.
Switching characteristics are independent of operating junction temperature. Notes:

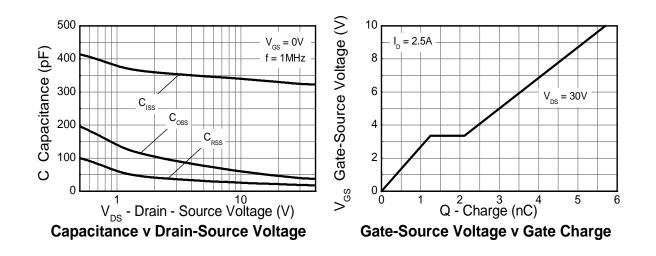


Typical Characteristics

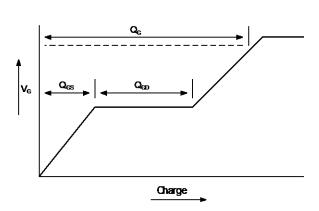




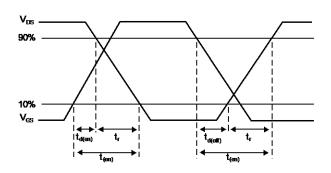
Typical Characteristics (continued)



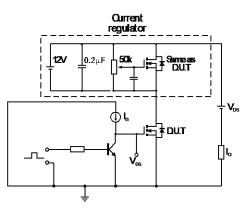
Test Circuit



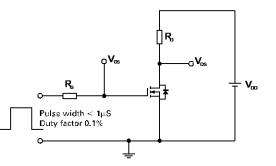
Basic gate charge waveform



Switching time waveforms



Gate charge test circuit

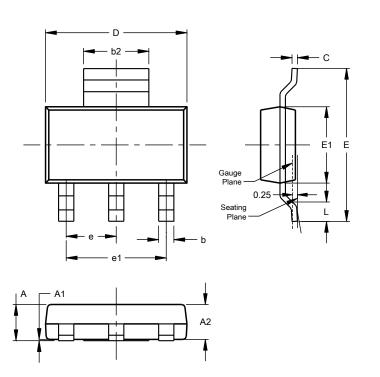


Switching time test circuit



Package Outline Dimensions

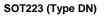
Please see http://www.diodes.com/package-outlines.html for the latest version.



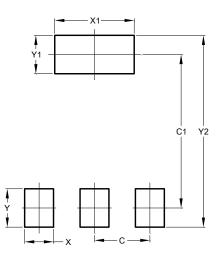
60	T222 (NI)		
SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
E	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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